William Gillin

List of Publications by Year
in descending order

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155 papers	4,665 citations	87843 38 h-index	114418 63 g-index
160 all docs	160 docs citations	160 times ranked	4505 citing authors

#	Article	IF	Citations
1	Magnetoresistance and efficiency measurements ofAlq3-based OLEDs. Physical Review B, 2007, 75, .	1.1	284
2	Direct measurement of the electronic spin diffusion length in a fully functional organic spinÂvalve by low-energy muon spin rotation. Nature Materials, 2009, 8, 109-114.	13.3	251
3	1.54 Î¼m electroluminescence from erbium (III) tris(8-hydroxyquinoline) (ErQ)-based organic light-emitting diodes. Applied Physics Letters, 1999, 75, 1380-1382.	1.5	177
4	Engineering spin propagation across a hybrid organic/inorganic interface using a polar layer. Nature Materials, 2011, 10, 39-44.	13.3	152
5	Magnetoresistance in organic light-emitting diode structures under illumination. Physical Review B, 2007, 76, .	1.1	132
6	Control of oxygen vacancies in ZnO nanorods by annealing and their influence on ZnO/PEDOT:PSS diode behaviour. Journal of Materials Chemistry C, 2018, 6, 1815-1821.	2.7	129
7	Erbium (III) tris(8-hydroxyquinoline) (ErQ): A potential material for silicon compatible 1.5 Î¼m emitters. Applied Physics Letters, 1999, 74, 798-799.	1.5	128
8	Organo-erbium systems for optical amplification at telecommunications wavelengths. Nature Materials, 2014, 13, 382-386.	13.3	120
9	Oxide phosphors for efficient light upconversion: Yb3+ and Er3+ co-doped Ln2BaZnO5 (Ln = Y, Gd). Journal of Materials Chemistry, 2010, 20, 3989.	6.7	106
10	Sprayâ€Deposited Liâ€Doped ZnO Transistors with Electron Mobility Exceeding 50 cm²/Vs. Advanced Materials, 2010, 22, 4764-4769.	11.1	105
11	Structural and Electrical Characterization of ZnO Films Grown by Spray Pyrolysis and Their Application in Thinâ€Film Transistors. Advanced Functional Materials, 2011, 21, 525-531.	7.8	100
12	Efficient oxide phosphors for light upconversion; green emission from Yb³⁺and Ho³⁺co-doped Ln₂BaZnO₅(Ln = Y, Gd). Journal of Materials Chemistry, 2011, 21, 1387-1394.	6.7	99
13	Characteristics of rareâ€earth element erbium implanted in silicon. Applied Physics Letters, 1989, 55, 432-433.	1.5	97
14	Quenching of Er(III) luminescence by ligand Câ€“H vibrations: Implications for the use of erbium complexes in telecommunications. Applied Physics Letters, 2006, 89, 111115.	1.5	95
15	A Singleâ€Device Universal Logic Gate Based on a Magnetically Enhanced Memristor. Advanced Materials, 2013, 25, 534-538.	11.1	95
16	Infrared organic light emitting diodes using neodymium tris-(8-hydroxyquinoline). Journal of Applied Physics, 2000, 88, 777-780.	1.1	90
17	The role of magnetic fields on the transport and efficiency of aluminum tris(8-hydroxyquinoline) based organic light emitting diodes. Journal of Applied Physics, 2007, 102, 073710.	1.1	79
18	Interdiffusion in InGaAs/GaAs quantum well structures as a function of depth. Journal of Applied Physics, 1993, 73, 3782-3786.	1.1	77

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19	Quenching of IR Luminescence of Erbium, Neodymium, and Ytterbium Î²-Diketonate Complexes by Ligand Câ”H and Câ”D Bonds. Journal of Physical Chemistry B, 2006, 110, 24476-24479.	1.2	71
20	Silicon-based organic light-emitting diode operating at a wavelength of 1.5 Î¼m. Applied Physics Letters, 2000, 77, 2271-2273.	1.5	67
21	980 nm electroluminescence from ytterbium tris(8-hydroxyquinoline). Organic Electronics, 2001, 2, 45-51.	1.4	67
22	Efficient white light emission by upconversion in Yb3+-, Er3+- and Tm3+-doped Y2BaZnO5. Chemical Communications, 2011, 47, 6263.	2.2	63
23	Importance of Spin-Orbit Interaction for the Electron Spin Relaxation in Organic Semiconductors. Physical Review Letters, 2013, 110, 216602.	2.9	62
24	Synthesis, Characterization, and Application of Coreâ€“Shell Co_{0.16}Fe_{2.84}O₄@NaYF₄(Yb, Er) and Fe₃O₄@NaYF₄(Yb, Tm) Nanoparticle as Trimodal (MRI, PET/SPECT,) Tj ETQq0 0 0 rgBT /Overlock	1.8	59
25	Electroluminescence of organolanthanide based organic light emitting diodes. Current Opinion in Solid State and Materials Science, 2001, 5, 481-486.	5.6	57
26	Oxide phosphors for light upconversion; Yb3+ and Tm3+ co-doped Y2BaZnO5. Journal of Applied Physics, 2011, 109, .	1.1	54
27	Influence of anneal atmosphere on ZnO-nanorod photoluminescent and morphological properties with self-powered photodetector performance. Journal of Applied Physics, 2013, 113, .	1.1	53
28	Elucidating the role of hyperfine interactions on organic magnetoresistance using deuterated aluminium tris(8-hydroxyquinoline). Physical Review B, 2009, 80, .	1.1	50
29	Solution processed SnO₂:Sb transparent conductive oxide as an alternative to indium tin oxide for applications in organic light emitting diodes. Journal of Materials Chemistry C, 2016, 4, 3563-3570.	2.7	49
30	Interdiffusion: A probe of vacancy diffusion in III-V materials. Physical Review B, 1997, 55, 15813-15818.	1.1	46
31	The effects of ion implantation on the interdiffusion coefficients in InxGa1â”xAs/GaAs quantum well structures. Journal of Applied Physics, 1993, 73, 1686-1692.	1.1	45
32	Effect of excited states and applied magnetic fields on the measured hole mobility in an organic semiconductor. Physical Review B, 2010, 82, .	1.1	45
33	The magnetic field effect on the transport and efficiency of group III tris(8-hydroxyquinoline) organic light emitting diodes. Journal of Applied Physics, 2008, 103, 103715.	1.1	44
34	Cooperative Infrared to Visible Up Conversion in Tb³⁺, Eu³⁺, and Yb³⁺ Containing Polymers. Advanced Materials, 2010, 22, 5356-5360.	11.1	41
35	Electronic and magnetic properties of the interface between metal-quinoline molecules and cobalt. Physical Review B, 2014, 89, .	1.1	41
36	Strain and interdiffusion in semiconductor heterostructures. Physical Review B, 1994, 50, 7495-7498.	1.1	40

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37	Luminescent Zinc(II) Complexes of Fluorinated Benzothiazol-2-yl Substituted Phenoxide and Enolate Ligands. Inorganic Chemistry, 2013, 52, 1379-1387.	1.9	40
38	Interdiffusion of the group-III sublattice in In-Ga-As-P/In-Ga-As-P and In-Ga-As/In-Ga-As heterostructures. Physical Review B, 1994, 50, 8071-8073.	1.1	39
39	Influence of High Hydrostatic Pressure on Alq₃, Gaq₃, and Inq₃ (q = 8-Hydroxyquinoline). Journal of Physical Chemistry B, 2009, 113, 14079-14086.	1.2	39
40	Infra-red and visible electroluminescence from ErQ based OLEDs. Synthetic Metals, 2000, 111-112, 35-38.	2.1	37
41	Morphological study of aluminumtris(8-hydroxyquinoline) thin films using infrared and Raman spectroscopy. Journal of Applied Physics, 2002, 92, 1902-1905.	1.1	36
42	Measurement of the size effect in the yield strength of nickel foils. Philosophical Magazine Letters, 2005, 85, 339-343.	0.5	36
43	Determining the influence of excited states on current transport in organic light emitting diodes using magnetic field perturbation. Physical Review B, 2010, 82, .	1.1	36
44	Concentration dependence of the up- and down-conversion emission colours of Er³⁺-doped Y₂O₃: a time-resolved spectroscopy analysis. Physical Chemistry Chemical Physics, 2014, 16, 20957-20963.	1.3	33
45	Effect of Fluorination on the Radiative Properties of Er3+ Organic Complexes: An Opto-Structural Correlation Study. Journal of Physical Chemistry C, 2013, 117, 23970-23975.	1.5	32
46	Radiative recombination mechanisms in aluminum tris(8-hydroxyquinoline): Evidence for triplet exciton recombination. Journal of Applied Physics, 2000, 88, 781-785.	1.1	29
47	The activation energy for GaAs/AlGaAs interdiffusion. Journal of Applied Physics, 1997, 82, 4842-4846.	1.1	27
48	Intrinsic Mobility Limit for Anisotropic Electron Transport in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Alq</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2008, 100, 116601.	2.9	27
49	Efficient sensitized emission in Yb(iii) pentachlorotropolonate complexes. Chemical Communications, 2013, 49, 1933.	2.2	27
50	Vacancy controlled interdiffusion of the group V sublattice in strained InGaAs/InGaAsP quantum wells. Applied Physics Letters, 1993, 63, 797-799.	1.5	26
51	Solution-Processable Carbon Nanoelectrodes for Single-Molecule Investigations. Journal of the American Chemical Society, 2016, 138, 2905-2908.	6.6	26
52	The effect of applied magnetic field on photocurrent generation in poly-3-hexylthiophene:[6,6]-phenyl C61-butyric acid methyl ester photovoltaic devices. Journal of Physics Condensed Matter, 2008, 20, 452203.	0.7	25
53	Modeling of positive and negative organic magnetoresistance in organic light-emitting diodes. Physical Review B, 2012, 86, .	1.1	24
54	Near-infrared photoluminescence of erbium tris(8-hydroxyquinoline) spin-coated thin films induced by low coherence light sources. Applied Physics Letters, 2007, 91, 021106.	1.5	23

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55	Carbon Nanotubeâ€Quantum Dot Nanohybrids: Coupling with Singleâ€Particle Control in Aqueous Solution. Small, 2017, 13, 1603042.	5.2	22
56	Type-II InAs/GaAsSb Quantum Dot Solar Cells With GaAs Interlayer. IEEE Journal of Photovoltaics, 2018, 8, 741-745.	1.5	22
57	1.5 Î¼m electroluminescence from organic light emitting diodes integrated on silicon substrates. Optical Materials, 2001, 17, 161-163.	1.7	21
58	Magnetoresistance in triphenyl-diamine derivative blue organic light emitting devices. Journal of Applied Physics, 2008, 103, 043706.	1.1	21
59	Spectroscopic study of Mq3 (M=Al, Ga, In, q=8-hydroxyquinolinate) at high pressure. Journal of Luminescence, 2009, 129, 1835-1839.	1.5	21
60	Nonradiative De-excitation Mechanisms in Long-Lived Erbium(III) Organic Compounds ErxY1-x[(p-CF3-C6F4)2PO2]3. Journal of Physical Chemistry B, 2009, 113, 7474-7481.	1.2	21
61	Intermixing in GaAsSb/GaAs single quantum wells. Journal of Applied Physics, 1998, 84, 4017-4019.	1.1	20
62	Importance of intramolecular electron spin relaxation in small molecule semiconductors. Physical Review B, 2011, 84, .	1.1	20
63	Ambipolar Charge Transport in â€œTraditionalâ€•Organic Hole Transport Layers. Advanced Materials, 2012, 24, 2278-2283.	11.1	20
64	Modelling of organic magnetoresistance as a function of temperature using the triplet polaron interaction. Synthetic Metals, 2011, 161, 628-631.	2.1	19
65	Enhanced 1.54-Î¼m photo- and electroluminescence based on a perfluorinated Er(III) complex utilizing an iridium(III) complex as a sensitizer. Light: Science and Applications, 2020, 9, 32.	7.7	19
66	Thermal processing of strained GaInAs/GaAs high hole mobility transistor structures. Applied Physics Letters, 1990, 56, 1116-1118.	1.5	18
67	On the diffusion of lattice matched InGaAs/InP microstructures. Journal of Applied Physics, 2003, 93, 3881-3885.	1.1	18
68	Reduced hole mobility due to the presence of excited states in poly-(3-hexylthiophene). Applied Physics Letters, 2008, 93, 233306.	1.5	18
69	Separating the roles of electrons and holes in the organic magnetoresistance of aluminum tris(8-hydroxyquinoline) organic light emitting diodes. Journal of Applied Physics, 2008, 104, 083703.	1.1	18
70	Sensitization, energy transfer and infra-red emission decay modulation in Yb3+-doped NaYF4 nanoparticles with visible light through a perfluoroanthraquinone chromophore. Scientific Reports, 2017, 7, 5066.	1.6	17
71	Measurement of the intersystem crossing rate in aluminum tris(8-hydroxyquinoline) and its modulation by an applied magnetic field. Journal of Applied Physics, 2009, 106, 043511.	1.1	16
72	An optical study of interdiffusion in ZnSe/ZnCdSe. Applied Physics Letters, 1996, 69, 1579-1581.	1.5	15

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73	Evidence for erbium-erbium energy migration in erbium(III) bis(perfluoro-p-tolyl)phosphinate. Applied Physics Letters, 2008, 92, 103303.	1.5	15
74	The role of interfaces in organic spin valves revealed through spectroscopic and transport measurements. Physica Status Solidi (B): Basic Research, 2012, 249, 9-17.	0.7	15
75	Visible-Range Sensitization of Er³⁺-Based Infrared Emission from Perfluorinated 2-Acylphenoxide Complexes. Journal of Physical Chemistry Letters, 2014, 5, 1560-1563.	2.1	15
76	An organic multilevel non-volatile memory device based on multiple independent switching modes. Organic Electronics, 2014, 15, 1983-1989.	1.4	15
77	Functionalisation of ligands through click chemistry: long-lived NIR emission from organic Er(<scp>iii</scp>) complexes with a perfluorinated core and a hydrogen-containing shell. RSC Advances, 2017, 7, 128-131.	1.7	15
78	Rutherford backscattering and secondary ion mass spectrometry studies of erbium implanted silicon. Solid State Communications, 1991, 77, 907-910.	0.9	14
79	Thermal interdiffusion in InGaAs/GaAs strained quantum wells as a function of doping density. Superlattices and Microstructures, 1991, 9, 39-42.	1.4	14
80	Control of defects in C+, Ge+, and Er+ implanted Si using post amorphization and solid phase regrowth. Nuclear Instruments & Methods in Physics Research B, 1995, 96, 265-270.	0.6	14
81	Effect of strain on the interdiffusion of InGaAs/GaAs heterostructures. Journal of Applied Physics, 1999, 85, 790-793.	1.1	14
82	Electroluminescence from5D0Â7FJand5D1Â7FJ(J= 0â€“4) transitions with a europium complex as emitter. Journal Physics D: Applied Physics, 2004, 37, 531-534.	1.3	14
83	Strong luminescence from erbium in Si/Si1â€“xGex/Si quantum well structures. Electronics Letters, 1997, 33, 1182.	0.5	13
84	Interdiffusion in InGaAs/GaAs: The effect of growth conditions. Journal of Applied Physics, 1998, 84, 232-236.	1.1	13
85	Near IR luminescent rare earth 3,4,5,6-tetrafluoro-2-nitrophenoxide complexes: Synthesis, X-ray crystallography and spectroscopy. Polyhedron, 2008, 27, 1503-1510.	1.0	13
86	Fitting the magnetoresponses of the OLED using polaron pair model to obtain spin-pair dynamics and local hyperfine fields. Scientific Reports, 2020, 10, 16806.	1.6	13
87	The effects of silicon and beryllium on the interdiffusion of GaAs/ AlxGa1â^'xAs and InxGa1â^'xAs/GaAs quantum well structures. Journal of Applied Physics, 1993, 73, 7715-7719.	1.1	12
88	The Fermi level effect in IIIâ€“V intermixing: The final nail in the coffin?. Journal of Applied Physics, 1997, 81, 2179-2184.	1.1	12
89	Erbium bis(pentafluorophenyl)phosphinate: a new hybrid material with unusually long-lived infrared luminescence. Journal of Materials Science: Materials in Electronics, 2009, 20, 430-434.	1.1	11
90	The Effect of Injection Layers on a Room Temperature Organic Spin Valve. IEEE Transactions on Magnetics, 2010, 46, 1307-1310.	1.2	11

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91	The effect of deuteration on organic magnetoresistance. Synthetic Metals, 2011, 161, 608-612.	2.1	11
92	Hole-exciton interaction induced high field decay of magneto-electroluminescence in Alq3-based organic light-emitting diodes at room temperature. Applied Physics Letters, 2016, 108, .	1.5	11
93	Waferâ€Scale Graphene Anodes Replace Indium Tin Oxide in Organic Lightâ€Emitting Diodes. Advanced Optical Materials, 2022, 10, 2101675.	3.6	11
94	Organic Chromophores-Based Sensitization of NIR-Emitting Lanthanides. Fundamental Theories of Physics, 2015, , 1-100.	0.1	9
95	The effect of gallium implantation on the intermixing of InGaAs/GaAs strained quantum wells. Solid State Communications, 1993, 85, 197-198.	0.9	8
96	Diffusion of ion beam created vacancies and their effect on intermixing: A gamblerâ€™s ruin approach. Journal of Applied Physics, 1994, 76, 3367-3371.	1.1	8
97	Diffusion in semiconductors. Computational Materials Science, 1998, 11, 96-100.	1.4	8
98	Concentration dependent interdiffusion in InGaAsâˆ•GaAs as evidenced by high resolution x-ray diffraction and photoluminescence spectroscopy. Journal of Applied Physics, 2005, 97, 013536.	1.1	8
99	High sensitization efficiency and energy transfer routes for population inversion at low pump intensity in Er organic complexes for IR amplification. Scientific Reports, 2018, 8, 3226.	1.6	8
100	Thermal interdiffusion in InGaAs/GaAs and GaAsSb/GaAs strained quantum wells as a function of doping density. Optical and Quantum Electronics, 1991, 23, S975-S980.	1.5	7
101	Reactive formation of cobalt silicide on single-crystal silicon under rapid electron beam heating. Applied Surface Science, 1992, 59, 55-62.	3.1	7
102	Comparative study of silicon nitride encapsulated and phosphine overpressure annealing on the interdiffusion of InxGa1âˆ’xAsâ€‰InxGa1âˆ’xAsyP1âˆ’y heterostructures. Journal of Applied Physics, 1995, 77, 1463-1465.	1.1	7
103	A new laser pain threshold model detects a faster onset of action from a liquid formulation of 1 g paracetamol than an equivalent tablet formulation. British Journal of Clinical Pharmacology, 2002, 53, 43-47.	1.1	7
104	The transition from bipolaron to triplet-polaron magnetoresistance in a single layer organic semiconductor device. Organic Electronics, 2014, 15, 1711-1716.	1.4	7
105	Thermal processing of GaAsSb/GaAs low-dimensional strained-layer structures. Superlattices and Microstructures, 1990, 7, 359-361.	1.4	6
106	Contactless electro-reflectance study of interdiffusion in heat-treated single quantum wells. Journal of Physics Condensed Matter, 1998, 10, 9865-9874.	0.7	6
107	Experimental studies on the conduction mechanism and electrical properties of the inverted Ba doped ZnO nanoparticles based memristor. Applied Physics Letters, 2019, 115, 073505.	1.5	6
108	Enhanced 1.54 Î¼m luminescence of a perfluorinated erbium complex sensitized by perfluorinated Pt(<scp>ii</scp>) and Zn(<scp>ii</scp>) phthalocyanines with 980 nm emission. Journal of Materials Chemistry C, 2021, 9, 456-465.	2.7	6

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109	Disorder-induced mixing of InGaAs/InP multiple quantum wells by phosphorus implantation for optical waveguides. Semiconductor Science and Technology, 1990, 5, 1063-1066.	1.0	5
110	Characterization of thermally annealed In0.2Ga0.8As/GaAs single quantum wells by optical spectroscopy and ion beam techniques. Applied Physics Letters, 1994, 64, 40-42.	1.5	5
111	Modelling and fitting the Polaron Pair Magnetoconductance model to obtain a realistic local hyperfine field in Tris-(8-hydroxyquinoline)aluminium based diodes. Scientific Reports, 2019, 9, 3439.	1.6	5
112	Aluminum promoted sulfidation of ammonium perrhenate: Presence of nanobattery in the ReS2 composite material based memcapacitor. Chemical Engineering Journal, 2020, 392, 123745.	6.6	5
113	Prolonged and efficient near-infrared photoluminescence of a sensitized organic ytterbium-containing molecular composite. Journal of Materials Chemistry C, 2020, 8, 9502-9505.	2.7	5
114	Thermally induced change in the profile of GaAs/AlGaAs quantum wells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 332-336.	1.7	4
115	Photoluminescence and x-ray diffraction studies of the diffusion behavior of lattice matched InGaAs/InP heterostructures. Journal of Applied Physics, 2003, 94, 988-992.	1.1	4
116	The importance of holes in aluminium tris-8-hydroxyquinoline (Alq3) devices with Fe and NiFe contacts. Applied Physics Letters, 2014, 104, 013303.	1.5	4
117	Annealing and doping-dependent magnetoresistance in single layer poly(3-hexyl-thiophene) organic semiconductor device. Organic Electronics, 2015, 17, 51-56.	1.4	4
118	Continuous Tuning of Organic Phosphorescence by Diluting Triplet Diffusion at the Molecular Level. Journal of Physical Chemistry Letters, 2018, 9, 2022-2024.	2.1	4
119	Room temperature synthesis of ReS₂through aqueous perrhenate sulfidation. Journal of Physics Condensed Matter, 2018, 30, 055702.	0.7	4
120	Experimental Studies on the Dynamic Memcapacitance Modulation of the ReO3@ReS2 Composite Material-Based Diode. Nanomaterials, 2020, 10, 2103.	1.9	4
121	Lattice site location and outdiffusion of mercury implanted in GaAs. Nuclear Instruments & Methods in Physics Research B, 1991, 59-60, 1090-1093.	0.6	3
122	Photoluminescence of deep levels in ionâ€implanted AlxGa1â^'xAs. Applied Physics Letters, 1991, 58, 1404-1406.	1.5	3
123	Photoluminescence of acceptor states in mercury implanted gallium arsenide. Journal of Applied Physics, 1992, 71, 2021-2022.	1.1	3
124	Improved electron injection into Alq3based devices using a thin Erq3injection layer. Journal Physics D: Applied Physics, 2008, 41, 085108.	1.3	3
125	Field-induced single-ion magnetic behaviour in a highly luminescent Er3+ complex. Materials Chemistry and Physics, 2015, 160, 429-434.	2.0	3
126	Enhancing the sensitization efficiency of erbium doped organic complexes by heavy halogen substitution. Journal of Materials Chemistry C, 2018, 6, 7012-7017.	2.7	3

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127	Bright and Efficient Sensitized Near-Infrared Photoluminescence from an Organic Neodymium-Containing Composite Material System. Journal of the American Chemical Society, 2021, 143, 17915-17919.	6.6	3
128	Two-Step Synthesis of Bismuth-Based Hybrid Halide Perovskite Thin-Films. Materials, 2021, 14, 7827.	1.3	3
129	The effects of air-semiconductor depletion on hall effect profiling of ion-implanted semiconductors. Solid-State Electronics, 1989, 32, 1045-1047.	0.8	2
130	The use of Hall effect profiling to monitor the reactivation of silicon implants after oxygen implantation in gallium arsenide. Vacuum, 1989, 39, 1149-1151.	1.6	2
131	Vacancy controlled interdiffusion in IIIâ€“V heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 21, 281-283.	1.7	2
132	Comparison of the effects of ion implantation induced interdiffusion in GaAs/AlGaAs and InGaAs/GaAs single quantum wells. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 747-750.	0.6	2
133	Characterization of interdiffusion around miscibility gap of lattice matched InGaAsâˆ•InP quantum wells by high resolution x-ray diffraction. Journal of Applied Physics, 2007, 101, 013502.	1.1	2
134	Low temperature magnetic field effects on the efficiency of aluminium tris(8-hydroxyquinoline) based organic light emitting diodes in the absence of magnetoresistance. Synthetic Metals, 2013, 173, 46-50.	2.1	2
135	Disorder-induced mixing of InGaAs/InP multiple quantum wells by phosphorus implantation for optical wave-guides. Semiconductor Science and Technology, 1990, 5, 1146-1146.	1.0	1
136	1.5 Î¼m Luminescence from ErQ Based Organic Light Emitting Diodes. Materials Research Society Symposia Proceedings, 1999, 558, 481.	0.1	1
137	Ferromagnetic-organic interfacial states and their role on low voltage current injection in tris-8-hydroxyquinloline (Alq3) organic spin valves. Applied Physics Letters, 2014, 105, 203301.	1.5	1
138	Understanding the role of electron and hole trions on current transport in aluminium tris(8-hydroxyquinoline) using organic magnetoresistance. Applied Physics Letters, 2014, 104, 043307.	1.5	1
139	Impurity effects on charge transport and magnetoconductance in a single layer poly(3-hexyl-thiophene) device. Applied Physics Letters, 2016, 108, 203301.	1.5	1
140	Manipulation of Molecular Vibrations on Condensing Er3+ State Densities for 1.5 Î¼m Application. Journal of Physical Chemistry Letters, 2021, 12, 9620-9625.	2.1	1
141	Effect of thermal diffusion on the excitonic reflectivity spectra of InGaAs/GaAs quantum wells. European Physical Journal Special Topics, 1993, 03, C5-291-C5-294.	0.2	1
142	Optical Waveguides In GaAlAs/GaAs And GaInAs/InP Multiquantum Well Structures. , 1990, , .		0
143	<title>Effect of controlled vacancy injection by ion implantation on the intermixing of InGa/GaAs quantum wells</title>. , 1992, , .		0
144	Interdiffusion and thermally induced strain relaxation in GaAs/In0.2Ga0.8As/GaAs single quantum well structures. Nuclear Instruments & Methods in Physics Research B, 1994, 85, 192-196.	0.6	0

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145	The Effect of Co-Dopants on the Photoluminescence of Er3+ in Silicon. Materials Research Society Symposia Proceedings, 1995, 392, 217.	0.1	0
146	Evidence for Non-Equilibrium Vacancy Concentrations Controlling Interdiffusion in III-V Materials. Materials Research Society Symposia Proceedings, 1998, 527, 401.	0.1	0
147	The photoluminescence temperature dependence of aluminium tris(8-hydroxyquinoline) as a function of excitation energy. Materials Research Society Symposia Proceedings, 1999, 558, 421.	0.1	0
148	1.5 Î½m Luminescence from ErQ based Organic Light Emitting Diodes. Materials Research Society Symposia Proceedings, 1999, 561, 211.	0.1	0
149	Organolanthanide-based infrared-light-emitting devices. , 2000, , .		0
150	Hybrid silicon-organic light-emitting diodes for 1.5-Î¼m optoelectronics. , 2001, 4105, 265.		0
151	‹title›Photoluminescence relaxation kinetics in vapor etched porous silicon‹/title›. , 2006, 6344, 286.		0
152	Novel Infrared Emitter for Low Cost Optical Devices. , 2007, , .		0
153	High-pressure study of non-radiative de-excitation mechanisms in perfluorinated organic erbium(III) phosphinates. Journal of Physics: Conference Series, 2010, 215, 012042.	0.3	0
154	Understanding asymmetric magnetoconductance in OLEDs: The effects of gradient magnetic fields. Organic Electronics, 2021, , 106251.	1.4	0
155	Waferâ€Scale Graphene Anodes Replace Indium Tin Oxide in Organic Lightâ€Emitting Diodes (Advanced) Tj ETQq1 1 0.784314 rgBT /	3.6	0